

ABSTRACT OF THE DISCLOSURE

Without forming a silicide film on a surface of a photodiode PD formation portion and a surface of a drain portion of a reset transistor T1 having an impurity region as a drain connected to an impurity region of the photodiode PD, the silicide film is formed on a surface of a source portion of the reset transistor T1 and a surface of a source/drain portion of other MOS transistors.

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